

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	8	tripple\$1well or tripple adj3 well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:13
S2	85853	n\$well or n adj5 well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:20
S3	71762	p adj4 (substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 11:24
S4	126255	cmos or c\$1mos or bi\$1cmos or cmos\$1bicmos or bicmos\$1cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:21
S5	14706	complement\$6 adj8 (mos or mosfet or fet or mis or misfet or field adj5 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:24
S6	132885	S4 or S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:24
S7	65693	(arsenic or n\$1type) near15 (implant\$6 or dop\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:26
S8	139284	S2 or S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:26

S9	29368	S8 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:27
S10	11557	S9 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:27
S11	119600	epi\$1si or epi\$1silicon or epitax\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 17:39
S12	3822	S10 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:29
S13	18457	S8 same S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:29
S14	2373	S13 and S6 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:46
S15	3052	triple\$1well or triple adj7 well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:17
S16	278	S15 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:48

S17	58017	(nnp or pnp or vnnp or vnpn or bjt or bipolar adj3 (transistor or device)) and (p\$1mos or n\$1mos or mos or mos\$1fet or mis or misfet or fet or n\$1fet or p\$1fet or field adj3 effect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:52
S18	173599	S6 or S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:53
S19	143	S16 and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 14:53
S20	313	S15 and (S11 or epi or epi\$1layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:18
S21	170	S20 not S19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 16:18
S22	1614	(438/199 or 438/202 or 438/222 or 438/223 or 438/224 or 438/234).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 17:37
S23	140152	epi\$1si or epi\$1silicon or epitax\$5 or epi or epi adj3 (layer or film or semiconductor or si or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 17:41
S24	712	S22 and S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 11:26

S25	17022	arsenic near10 implant\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 11:23
S26	98062	(p or p\$1type) adj7 (substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 11:25
S27	1614	(438/199 or 438/202 or 438/222 or 438/223 or 438/224 or 438/234).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 11:26
S28	140251	epi\$1si or epi\$1silicon or epitax\$5 or epi or epi adj3 (layer or film or semiconductor or si or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 11:26
S29	712	S27 and S28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 11:26
S30	253	S25 and S26 and S29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 12:21
S31	6	((("5880014") or ("6366499") or ("20030020106")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 12:21